

Fast switching diode chip in EMCON 3 -Technology

Features:

- 650V EMCON 3 technology 65 µm chip
- Soft, fast switching
- Low reverse recovery charge
- Small temperature coefficient
- Qualified according to JEDEC for target applications

Recommended for:

Power module



Applications:

- Drives
- White goods
- Resonant applications

Chip Type	V _R	/ _{Fn} ¹⁾	Die Size	Package
SIDC26D65C8	650V	100A	6.53 x 4.02 mm ²	sawn on foil

"nominal forward current at Tc = 100°C, not subject to production test - verified by design/characterisation

Mechanical Parameters

Die size		6.53 x 4.02		
Area total		26.25	mm ²	
Anode pad size		5.83 x 3.32		
Thickness		65	μm	
Wafer size		200	mm	
Max. possible chips pe	er wafer	1032		
Passivation frontside		Photoimide		
Pad metal		3200 nm AlSiCu		
Backside metal		Ni Ag –system		
Die bond		Electrically conductive epoxy glue and soft solder		
Wire bond		Al, ≤500µm		
Reject ink dot size		Ø 0.65mm; max 1.2mm		
Storage environment	for original and sealed MBB bags	Ambient atmosphere air, Temperature 17°C – 2 < 6 month	•	
	for open MBB bags	s Acc. to IEC62258-3: Atmosphere >99% Nitrogen o Humidity <25%RH, Temperature 17°C – 25°C, <		



Maximum Ratings

Parameter	Symbol	Condition	Value	Unit
Repetitive peak reverse voltage	V _{RRM}	<i>T</i> _{vj} = 25 °C	650	V
Continuous forward current	I _F	<i>T</i> _{vj} < 150°C	1)	•
Maximum repetitive forward current ²⁾	I _{FRM}	<i>T</i> _{vj} < 150°C	200	A
Operating junction temperature	T _{vj}		-40+175	°C

¹) depending on thermal properties of assembly

²) not subject to production test - verified by design/characterisation

Static Characteristics (tested on wafer), T_{vj} = 25 °C

Parameter	Symbol	Conditions	Value			Unit
Farameter			min.	typ.	max.	Unit
Reverse leakage current	I _R	V _R =650V			1.2	μA
Cathode-Anode breakdown Voltage	V _{BR}	I _R =0.25mA	650			V
Forward voltage drop	V _F	/ _F =30A	1.03	1.17	1.32	

Electrical Characteristics (not subject to production test - verified by design/characterization)

Parameter		Symbol Conditions	Conditiono	Value			Unit
			min.	typ.	max.		
Forward voltage	<i>T</i> _{vj} = 25°C	V	1 - 100 4		1.55	1.95	V
drop	<i>T</i> _{vj} = 150°C	V _F	<i>I</i> _F =100A		1.45		V

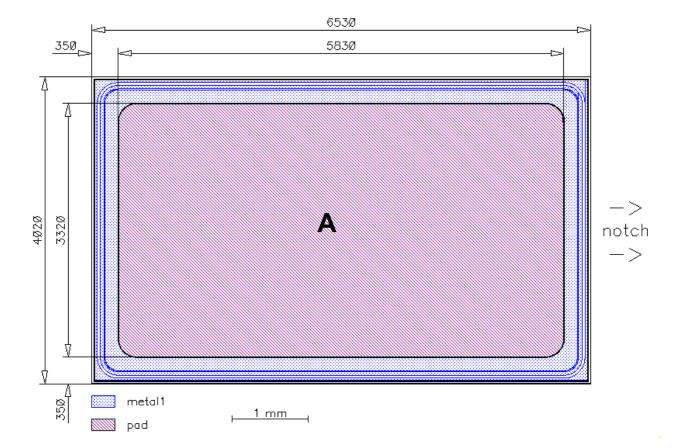
Further Electrical Characteristics

Switching characteristics and thermal properties are depending strongly on module design and mounting technology and can therefore not be specified for a bare die.

This chip data sheet refers to the device data sheet	FS100R07N3E4_B11	Rev. 2.0
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Chip Drawing



Die-Size 6530 um x 4020 um

A: Anode pad



Description

AQL 0,65 for visual inspection according to failure catalogue

Electrostatic Discharge Sensitive Device according to MIL-STD 883

Revision History

Version	Subjects (major changes since last revision)	Date

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